

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ max	I_D max $T_A = +25^\circ\text{C}$
100V	160m Ω @ $V_{GS} = 10\text{V}$	2.6A
	200m Ω @ $V_{GS} = 4.5\text{V}$	2.3A

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- Power Management Functions
- Battery Operated Systems and Solid-State Relays
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc.

Features and Benefits

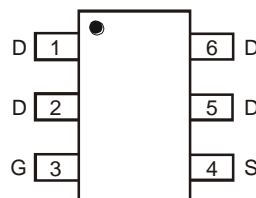
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

Mechanical Data

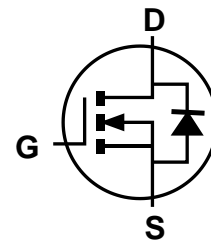
- Case: TSOT26
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 **(e3)**
- Weight: 0.015 grams (Approximate)



Top View



Top View
Pin-Out



Equivalent Circuit

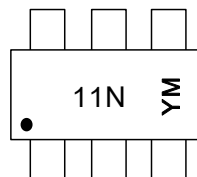
Ordering Information (Note 4)

Part Number	Case	Packaging
DMN10H170SVT-7	TSOT26	3,000/Tape & Reel
DMN10H170SVT-13	TSOT26	10,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information

TSOT26



11N = Product Type Marking Code
 YM = Date Code Marking
 Y or Y = Year (ex: B = 2014)
 M = Month (ex: 9 = September)

Date Code Key

Year	2014	2015	2016	2017	2018	2019	2020	2021
Code	B	C	D	E	F	G	H	I

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	100	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	T _A = +25°C	I _D	2.6	A
		T _A = +70°C		2.1	
Pulsed Drain Current (10µs pulse, duty cycle ≤1%)			I _{DM}	11.2	A
Maximum Body Diode Continuous Current (Note 6)			I _S	2.0	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Total Power Dissipation	(Note 5)	P _D		1.2	W
	(Note 6)			1.7	
Thermal Resistance, Junction to Ambient	(Note 5)	R _{θJA}		101	°C/W
	(Note 6)			73	
Thermal Resistance, Junction to Case	(Note 6)	R _{θJC}		15	
Operating and Storage Temperature Range			T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	100	—	—	V	V _{GS} = 0V, I _D = 250µA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1.0	µA	V _{DS} = 100V, V _{GS} = 0V
Gate-Body Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(th)}	1.0	2.0	3.0	V	V _{DS} = V _{GS} , I _D = 250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	115	160	mΩ	V _{GS} = 10V, I _D = 5.0A
		—	124	200		V _{GS} = 4.5V, I _D = 5.0A
Diode Forward Voltage	V _{SD}	—	0.9	1.0	V	V _{GS} = 0V, I _S = 10A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	1,167	—	pF	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	36	—		
Reverse Transfer Capacitance	C _{rss}	—	25	—		
Gate Resistance	R _g	—	1.3	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	4.9	—	nC	V _{DS} = 80V, I _D = 12.8A
Total Gate Charge (V _{GS} = 10V)	Q _g	—	9.7	—		
Gate-Source Charge	Q _{gs}	—	2.0	—		
Gate-Drain Charge	Q _{gd}	—	2.0	—		
Turn-On Delay Time	t _{D(on)}	—	10	—	nS	V _{DD} = 50V, V _{GS} = 10V, R _G = 25Ω, I _D = 12.8A
Turn-On Rise Time	t _r	—	11	—		
Turn-Off Delay Time	t _{D(off)}	—	42	—		
Turn-Off Fall Time	t _f	—	12	—		
Reverse Recovery Time	t _{rr}	—	30	—	nS	V _{GS} = 0V, I _S = 12.8A, di/dt = 100A/µs
Reverse Recovery Charge	Q _{rr}	—	35	—	nC	

- Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

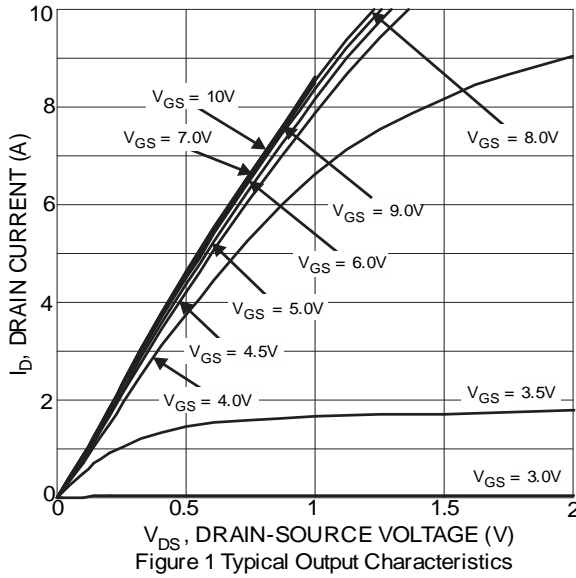


Figure 1 Typical Output Characteristics

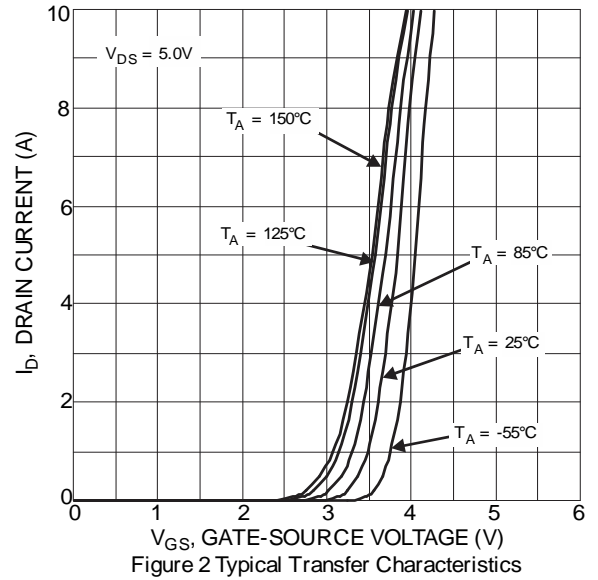


Figure 2 Typical Transfer Characteristics

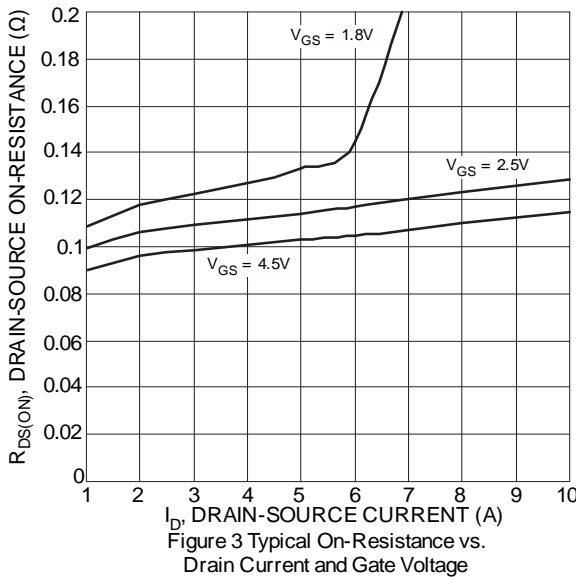


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

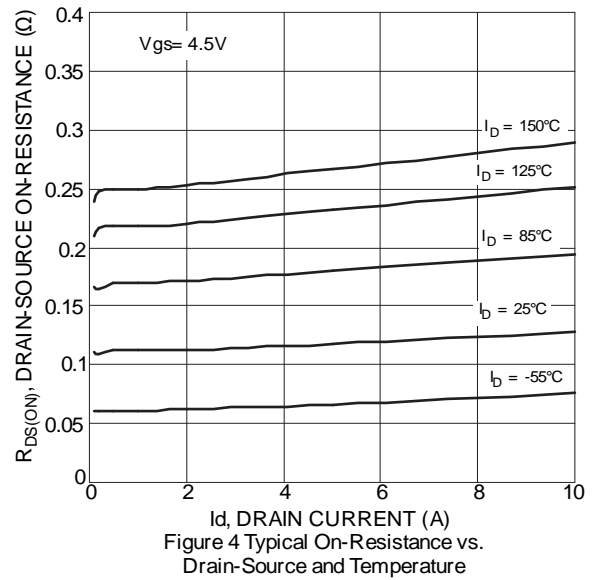


Figure 4 Typical On-Resistance vs. Drain-Source and Temperature

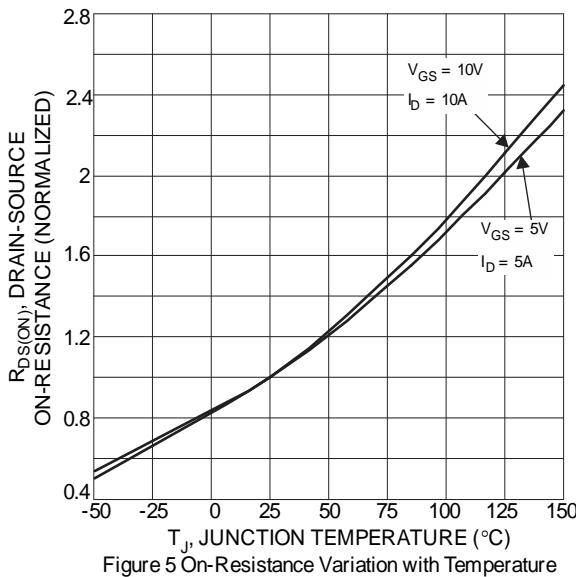


Figure 5 On-Resistance Variation with Temperature

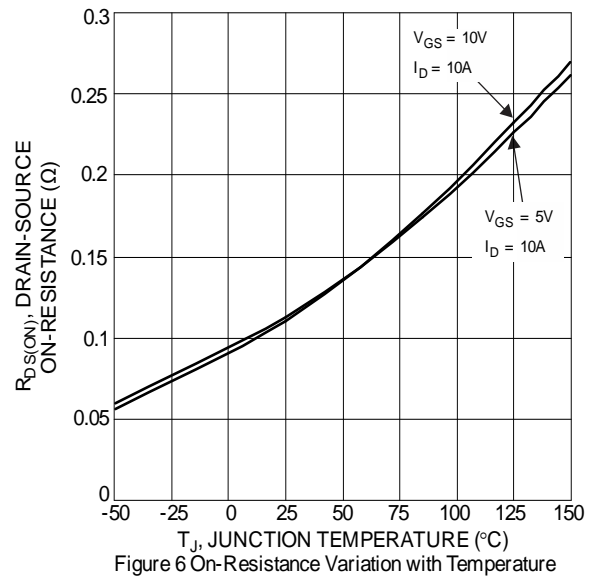


Figure 6 On-Resistance Variation with Temperature

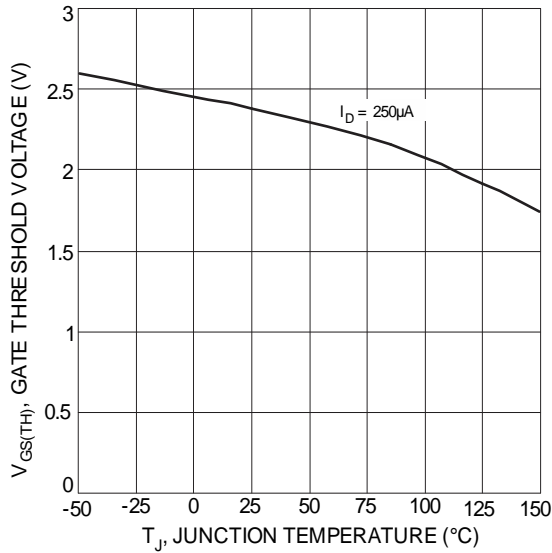


Figure 7 Gate Threshold Variation vs. Ambient Temperature

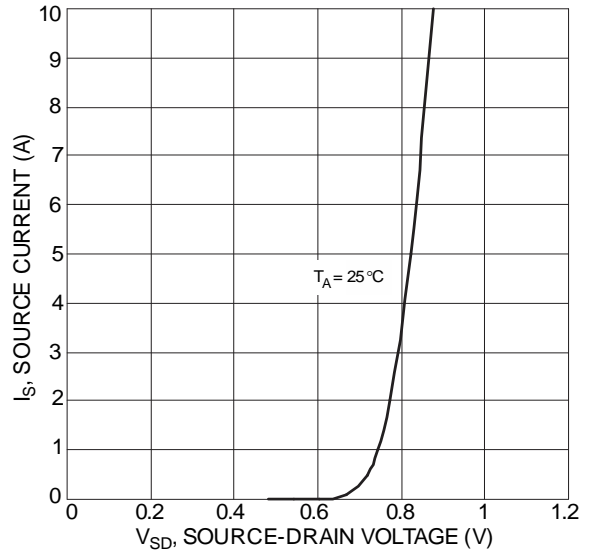


Figure 8 Diode Forward Voltage vs. Current

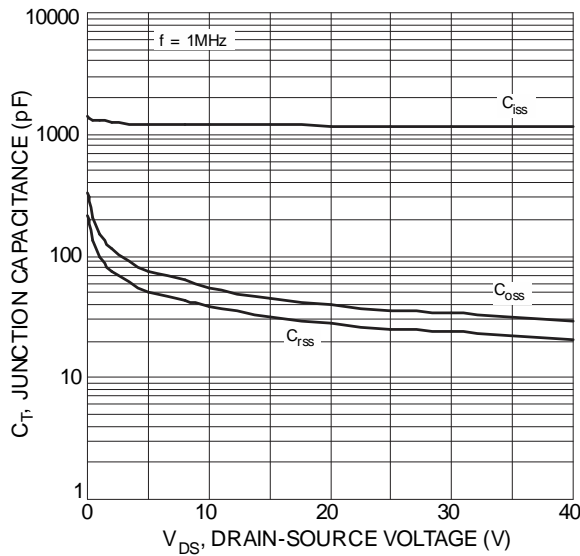


Figure 9 Typical Junction Capacitance

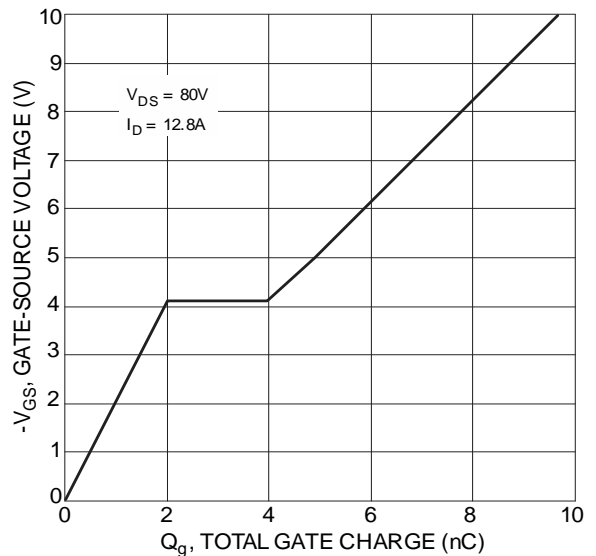


Figure 10 Gate-Charge Characteristics

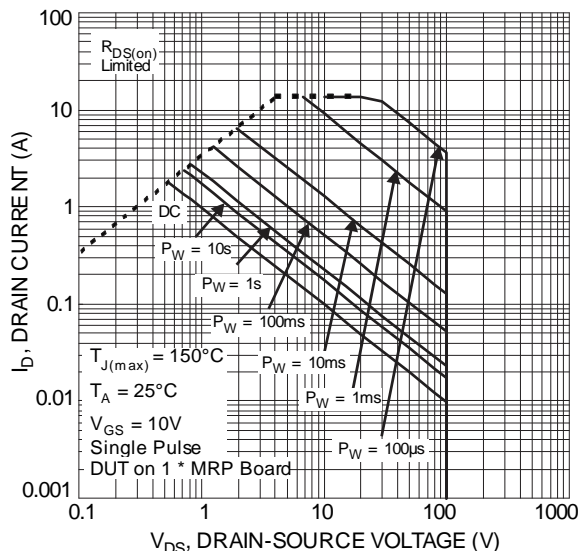
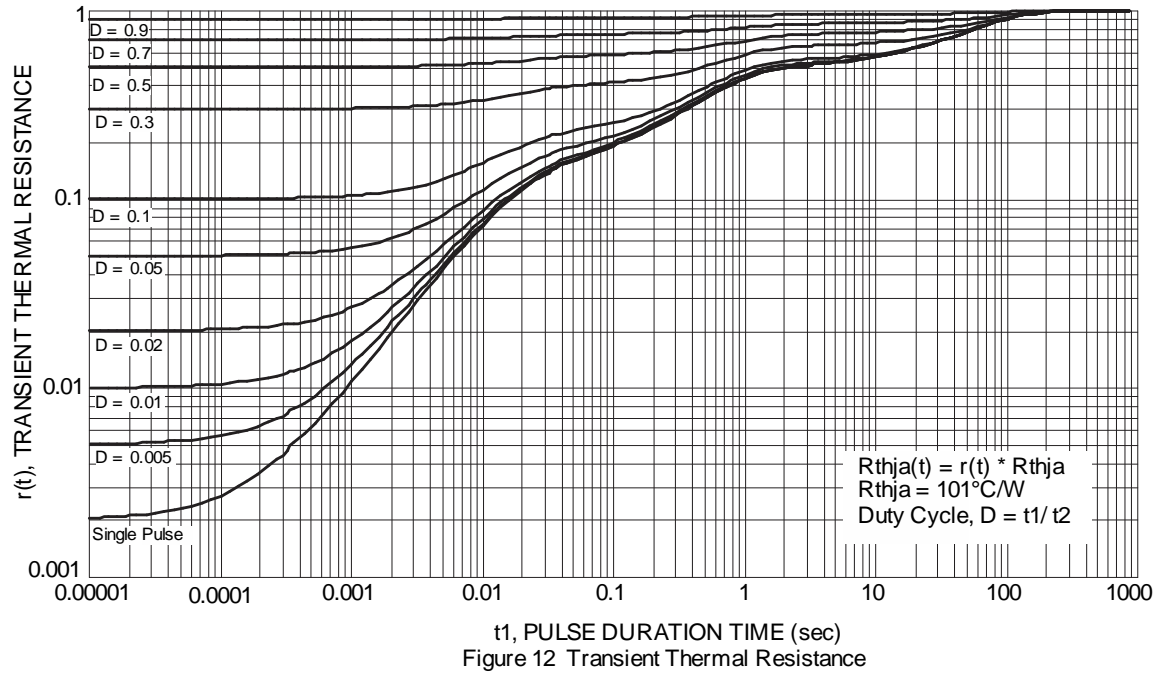
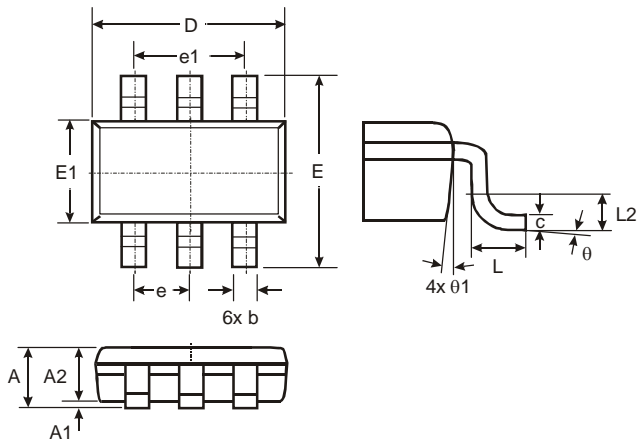


Figure 11 SOA, Safe Operation Area



Package Outline Dimensions

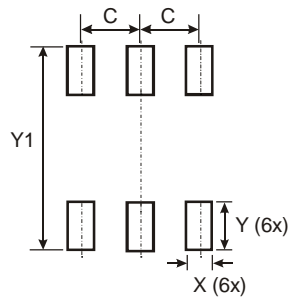
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



TSOT26			
Dim	Min	Max	Typ
A	-	1.00	-
A1	0.01	0.10	-
A2	0.84	0.90	-
D	-	-	2.90
E	-	-	2.80
E1	-	-	1.60
b	0.30	0.45	-
c	0.12	0.20	-
e	-	-	0.95
e1	-	-	1.90
L	0.30	0.50	-
L2	-	-	0.25
θ	0°	8°	4°
θ1	4°	12°	-
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	0.950
X	0.700
Y	1.000
Y1	3.199

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